Toshio Kamiya

List of Publications by Citations

236 papers	27,342 citations	74 h-index	163 g-index
249 ext. papers	29,538 ext. citations	4 avg, IF	6.9 L-index

#	Paper	IF	Citations
236	Room-temperature fabrication of transparent flexible thin-film transistors using amorphous oxide semiconductors. *Nature*, **2004**, 432, 488-92	50.4	5517
235	Thin-film transistor fabricated in single-crystalline transparent oxide semiconductor. *Science*, **2003**, 300, 1269-72	33.3	1534
234	Present status of amorphous In-Ga-Zn-O thin-film transistors. *Science and Technology of Advanced Materials*, **2010**, 11, 044305	7.1	1287
233	Iron-based layered superconductor: LaOFeP. *Journal of the American Chemical Society*, **2006**, 128, 10012-26	16.4	1051
232	High-mobility thin-film transistor with amorphous InGaZnO4 channel fabricated by room temperature rf-magnetron sputtering. *Applied Physics Letters*, **2006**, 89, 112123	3.4	944
231	Material characteristics and applications of transparent amorphous oxide semiconductors. *NPG Asia Materials*, **2010**, 2, 15-22	10.3	664
230	High-density electron anions in a nanoporous single crystal: [Ca24Al28O64]4+(4e-). *Science*, **2003**, 301, 626-9	33.3	638
229	Amorphous Oxide Semiconductors for High-Performance Flexible Thin-Film Transistors. *Japanese Journal of Applied Physics*, **2006**, 45, 4303-4308	1.4	589
228	p-channel thin-film transistor using p-type oxide semiconductor, SnO. *Applied Physics Letters*, **2008**, 93, 032113	3.4	491
227	Light-induced conversion of an insulating refractory oxide into a persistent electronic conductor. *Nature*, **2002**, 419, 462-5	50.4	386
226	Carrier transport and electronic structure in amorphous oxide semiconductor, a-InGaZnO4. *Thin Solid Films*, **2005**, 486, 38-41	2.2	385
225	Origins of High Mobility and Low Operation Voltage of Amorphous Oxide TFTs: Electronic Structure, Electron Transport, Defects and Doping. *Journal of Display Technology*, **2009**, 5, 273-288		371
224	Origins of threshold voltage shifts in room-temperature deposited and annealed a-InGaZnO thin-film transistors. *Applied Physics Letters*, **2009**, 95, 013502	3.4	295
223	Modeling of amorphous InGaZnO4 thin film transistors and their subgap density of states. *Applied Physics Letters*, **2008**, 92, 133503	3.4	289
222	Fabrication and photoresponse of a pn-heterojunction diode composed of transparent oxide semiconductors, p-NiO and n-ZnO. *Applied Physics Letters*, **2003**, 83, 1029-1031	3.4	288
221	Subgap states in transparent amorphous oxide semiconductor, InGaZnO, observed by bulk sensitive x-ray photoelectron spectroscopy. *Applied Physics Letters*, **2008**, 92, 202117	3.4	268
220	Trap densities in amorphous-InGaZnO4 thin-film transistors. *Applied Physics Letters*, **2008**, 92, 133512	3.4	254

219	Local coordination structure and electronic structure of the large electron mobility amorphous oxide semiconductor In-Ga-Zn-O: Experiment and ab initio calculations. *Physical Review B*, **2007**, 75,	3.3	252
218	Nickel-based oxyphosphide superconductor with a layered crystal structure, LaNiOP. *Inorganic Chemistry*, **2007**, 46, 7719-21	5.1	245
217	Defect passivation and homogenization of amorphous oxide thin-film transistor by wet O2 annealing. *Applied Physics Letters*, **2008**, 93, 192107	3.4	243
216	Carrier transport in transparent oxide semiconductor with intrinsic structural randomness probed using single-crystalline InGaO3(ZnO)5 films. *Applied Physics Letters*, **2004**, 85, 1993-1995	3.4	229
215	Crystal Structures, Optoelectronic Properties, and Electronic Structures of Layered Oxychalcogenides MCuOCh (M = Bi, La; Ch = S, Se, Te): Effects of Electronic Configurations of M3+ Ions. *Chemistry of Materials*, **2008**, 20, 326-334	9.6	227
214	Advantageous grain boundaries in iron pnictide superconductors. *Nature Communications*, **2011**, 2, 409	17.4	212
213	Ambipolar oxide thin-film transistor. *Advanced Materials*, **2011**, 23, 3431-4	24	207
212	Combinatorial approach to thin-film transistors using multicomponent semiconductor channels: An application to amorphous oxide semiconductors in In□Ga□Zn□O system. *Applied Physics Letters*, **2007**, 90, 242114	3.4	200
211	Epitaxial growth of high mobility Cu2O thin films and application to p-channel thin film transistor. *Applied Physics Letters*, **2008**, 93, 202107	3.4	193
210	Electronic structure of oxygen deficient amorphous oxide semiconductor a-InGaZnO4□ : Optical analyses and first-principle calculations. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 3098-3100		187
209	Tin monoxide as an s-orbital-based p-type oxide semiconductor: Electronic structures and TFT application. *Physica Status Solidi (A) Applications and Materials Science*, **2009**, 206, 2187-2191	1.6	185
208	Electronic Structures Above Mobility Edges in Crystalline and Amorphous In-Ga-Zn-O: Percolation Conduction Examined by Analytical Model. *Journal of Display Technology*, **2009**, 5, 462-467		185
207	Electronic structure of the amorphous oxide semiconductor a-InGaZnO4□ : Tauc□lorentz optical model and origins of subgap states. *Physica Status Solidi (A) Applications and Materials Science*, **2009** , 206, 860-867	1.6	183
206	Metallic state in a lime-alumina compound with nanoporous structure. *Nano Letters*, **2007**, 7, 1138-43	11.5	183
205	UV-detector based on pn-heterojunction diode composed of transparent oxide semiconductors, p-NiO/n-ZnO. *Thin Solid Films*, **2003**, 445, 317-321	2.2	183
204	Specific contact resistances between amorphous oxide semiconductor In□Ga□Zn□O and metallic electrodes. *Thin Solid Films*, **2008**, 516, 5899-5902	2.2	171
203	Effects of excess oxygen on operation characteristics of amorphous In-Ga-Zn-O thin-film transistors. *Applied Physics Letters*, **2011**, 99, 093507	3.4	166
202	Sputtering formation of p-type SnO thin-film transistors on glass toward oxide complimentary circuits. *Applied Physics Letters*, **2010**, 97, 072111	3.4	165

201	Amorphous oxide channel TFTs. *Thin Solid Films*, **2008**, 516, 1516-1522	2.2	155
200	Degenerate p-type conductivity in wide-gap LaCuOS1−xSex (x=0-1) epitaxial films. *Applied Physics Letters*, **2003**, 82, 1048-1050	3.4	155
199	Effects of Diffusion of Hydrogen and Oxygen on Electrical Properties of Amorphous Oxide Semiconductor, In-Ga-Zn-O. *ECS Journal of Solid State Science and Technology*, **2013**, 2, P5-P8	2	152
198	Factors controlling electron transport properties in transparent amorphous oxide semiconductors. *Journal of Non-Crystalline Solids*, **2008**, 354, 2796-2800	3.9	152
197	Amorphous InGaZnO coplanar homojunction thin-film transistor. *Applied Physics Letters*, **2009**, 94, 133502	3.4	150
196	Growth, structure and carrier transport properties of Ga2O3 epitaxial film examined for transparent field-effect transistor. *Thin Solid Films*, **2006**, 496, 37-41	2.2	142
195	Depth analysis of subgap electronic states in amorphous oxide semiconductor, a-In-Ga-Zn-O, studied by hard x-ray photoelectron spectroscopy. *Journal of Applied Physics*, **2011**, 109, 073726	2.5	141
194	Highly stable amorphous In-Ga-Zn-O thin-film transistors produced by eliminating deep subgap defects. *Applied Physics Letters*, **2011**, 99, 053505	3.4	139
193	Bipolar Conduction in SnO Thin Films. *Electrochemical and Solid-State Letters*, **2011**, 14, H13		132
192	Itinerant ferromagnetism in the layered crystals LaCoOX(X=P,As). *Physical Review B*, **2008**, 77,	3.3	129
191	Proton Conduction in In[sup 3+]-Doped SnP[sub 2]O[sub 7] at Intermediate Temperatures. *Journal of the Electrochemical Society*, **2006**, 153, A1604	3.9	129
190	Subgap states, doping and defect formation energies in amorphous oxide semiconductor a-InGaZnO4 studied by density functional theory. *Physica Status Solidi (A) Applications and Materials Science*, **2010**, 207, 1698-1703	1.6	127
189	Frontier of transparent oxide semiconductors. *Solid-State Electronics*, **2003**, 47, 2261-2267	1.7	123
188	Origin of definite Hall voltage and positive slope in mobility-donor density relation in disordered oxide semiconductors. *Applied Physics Letters*, **2010**, 96, 122103	3.4	121
187	Oligomerization of adenosine A2A and dopamine D2 receptors in living cells. *Biochemical and Biophysical Research Communications*, **2003**, 306, 544-9	3.4	118
186	Field-induced current modulation in epitaxial film of deep-ultraviolet transparent oxide semiconductor Ga2O3. *Applied Physics Letters*, **2006**, 88, 092106	3.4	117
185	Two-Dimensional Transition-Metal Electride Y2C. *Chemistry of Materials*, **2014**, 26, 6638-6643	9.6	113
184	Fabrication and characterization of heteroepitaxial p-n junction diode composed of wide-gap oxide semiconductors p-ZnRh2O4/n-ZnO. *Applied Physics Letters*, **2003**, 82, 823-825	3.4	112

183	Nickel-based phosphide superconductor with infinite-layer structure, BaNi2P2. *Solid State Communications*, **2008**, 147, 111-113	1.6	110
182	Biaxially textured cobalt-doped BaFe2As2 films with high critical current density over 1 MA/cm2 on MgO-buffered metal-tape flexible substrates. *Applied Physics Letters*, **2011**, 98, 242510	3.4	105
181	Fast Thin-Film Transistor Circuits Based on Amorphous Oxide Semiconductor. *IEEE Electron Device Letters*, **2007**, 28, 273-275	4.4	104
180	Superconductivity in Epitaxial Thin Films of Co-Doped SrFe2As2with Bilayered FeAs Structures and their Magnetic Anisotropy. *Applied Physics Express*, **2008**, 1, 101702	2.4	101
179	Hydrogen passivation of electron trap in amorphous In-Ga-Zn-O thin-film transistors. *Applied Physics Letters*, **2013**, 103, 202114	3.4	92
178	Optical and electrical properties of amorphous zinc tin oxide thin films examined for thin film transistor application. *Journal of Vacuum Science & Technology B*, **2008**, 26, 495		89
177	Heteroepitaxial growth and optoelectronic properties of layered iron oxyarsenide, LaFeAsO. *Applied Physics Letters*, **2008**, 93, 162504	3.4	88
176	Single-atomic-layered quantum wells built in wide-gap semiconductors LnCuOCh (Ln=lanthanide, Ch=chalcogen). *Physical Review B*, **2004**, 69,	3.3	88
175	Nickel-based layered superconductor, LaNiOAs. *Journal of Solid State Chemistry*, **2008**, 181, 2117-2120	3.3	86
174	Heavy hole doping of epitaxial thin films of a wide gap p-type semiconductor, LaCuOSe, and analysis of the effective mass. *Applied Physics Letters*, **2007**, 91, 012104	3.4	82
173	Three-dimensionally stacked flexible integrated circuit: Amorphous oxide/polymer hybrid complementary inverter using n-type a-In□Ga□Zn□O and p-type poly-(9,9-dioctylfluorene-co-bithiophene) thin-film transistors. *Applied Physics Letters*, **2010**, 96, 263509	3.4	81
172	High Critical Current Density 4 MA/cm2in Co-Doped BaFe2As2Epitaxial Films Grown on (La,Sr)(Al,Ta)O3Substrates without Buffer Layers. *Applied Physics Express*, **2010**, 3, 063101	2.4	81
171	Intermediate-Temperature Proton Conduction in Al[sup 3+]-Doped SnP[sub 2]O[sub 7]. *Journal of the Electrochemical Society*, **2007**, 154, B1265	3.9	81
170	Device characteristics improvement of a-In□Ga□Zn□O TFTs by low-temperature annealing. *Thin Solid Films*, **2010**, 518, 3017-3021	2.2	80
169	Femtosecond-laser-encoded distributed-feedback color center laser in lithium fluoride single crystals. *Applied Physics Letters*, **2004**, 84, 311-313	3.4	79
168	Wide-gap layered oxychalcogenide semiconductors: Materials, electronic structures and optoelectronic properties. *Thin Solid Films*, **2006**, 496, 8-15	2.2	77
167	Electron field emission from TiO2 nanotube arrays synthesized by hydrothermal reaction. *Applied Physics Letters*, **2006**, 89, 043114	3.4	76
166	A germanate transparent conductive oxide. *Nature Communications*, **2011**, 2, 470	17.4	75

165	Structural relaxation in amorphous oxide semiconductor, a-In-Ga-Zn-O. *Journal of Applied Physics*, **2012**, 111, 073513	2.5	74
164	Intrinsic excitonic photoluminescence and band-gap engineering of wide-gap p-type oxychalcogenide epitaxial films of LnCuOCh (Ln=La, Pr, and Nd; Ch=S or Se) semiconductor alloys. *Journal of Applied Physics*, **2003**, 94, 5805-5808	2.5	74
163	Breast cancer stem cells. *Breast Cancer*, **2010**, 17, 80-5	3.4	70
162	Electronic structure of oxygen dangling bond in glassy SiO2: the role of hyperconjugation. *Physical Review Letters*, **2003**, 90, 186404	7.4	70
161	Stability and high-frequency operation of amorphous InGaZnO thin-film transistors with various passivation layers. *Thin Solid Films*, **2012**, 520, 3778-3782	2.2	69
160	. *IEEE Electron Device Letters*, **2011**, 32, 1695-1697	4.4	69
159	Electromagnetic properties and electronic structure of the iron-based layered superconductor LaFePO. *Physical Review B*, **2008**, 77,	3.3	68
158	Josephson junction in cobalt-doped BaFe2As2 epitaxial thin films on (La,Sr)(Al,Ta)O3 bicrystal substrates. *Applied Physics Letters*, **2010**, 96, 142507	3.4	66
157	First-principles study of native point defects in crystalline indium gallium zinc oxide. *Journal of Applied Physics*, **2009**, 105, 093712	2.5	65
156	Atomically-flat, chemically-stable, superconducting epitaxial thin film of iron-based superconductor, cobalt-doped BaFe2As2. *Solid State Communications*, **2009**, 149, 2121-2124	1.6	65
155	Intense thermal field electron emission from room-temperature stable electride. *Applied Physics Letters*, **2005**, 87, 254103	3.4	65
154	Water-induced superconductivity in SrFe2As2. *Physical Review B*, **2009**, 80,	3.3	64
153	Electronic Structures and Device Applications of Transparent Oxide Semiconductors: What Is the Real Merit of Oxide Semiconductors?. *International Journal of Applied Ceramic Technology*, **2005**, 2, 285-294	2	60
152	Effects of post-annealing on (110) Cu2O epitaxial films and origin of low mobility in Cu2O thin-film transistor. *Physica Status Solidi (A) Applications and Materials Science*, **2009**, 206, 2192-2197	1.6	59
151	Photoelectron Spectroscopic Study of C12A7:e- and Alq3 Interface: The Formation of a Low Electron-Injection Barrier. *Journal of Physical Chemistry C*, **2007**, 111, 8403-8406	3.8	59
150	Optical and Carrier Transport Properties of Cosputtered ZnInSnO Films and Their Applications to TFTs. *Journal of the Electrochemical Society*, **2008**, 155, H390	3.9	57
149	Large Photoresponse in Amorphous InGaZnO and Origin of Reversible and Slow Decay. *Electrochemical and Solid-State Letters*, **2010**, 13, H324		54
148	Growth mechanism for single-crystalline thin film of InGaO3(ZnO)5 by reactive solid-phase epitaxy. *Journal of Applied Physics*, **2004**, 95, 5532-5539	2.5	54

147	Third-order optical nonlinearity originating from room-temperature exciton in layered compounds LaCuOS and LaCuOSe. *Applied Physics Letters*, **2004**, 84, 879-881	3.4	52
146	Localized and Delocalized Electrons in Room-Temperature Stable Electride [Ca24Al28O64]4+(O2-)2-x(e-)2x: Analysis of Optical Reflectance Spectra. *Journal of Physical Chemistry C*, **2008**, 112, 4753-4760	3.8	51
145	Amorphous InGaZn-O thin-film transistor with coplanar homojunction structure. *Thin Solid Films*, **2009**, 518, 1309-1313	2.2	50
144	Mechanism for Heteroepitaxial Growth of Transparent P-Type Semiconductor: LaCuOS by Reactive Solid-Phase Epitaxy. *Crystal Growth and Design*, **2004**, 4, 301-307	3.5	50
143	Excitonic blue luminescence from p-LaCuOSe/n-InGaZn5O8 light-emitting diode at room temperature. *Applied Physics Letters*, **2005**, 87, 211107	3.4	50
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141	High electron doping to a wide band gap semiconductor 12CaO·7Al2O3 thin film. *Applied Physics Letters*, **2007**, 90, 182105	3.4	48
140	Formation of inorganic electride thin films via site-selective extrusion by energetic inert gas ions. *Journal of Applied Physics*, **2005**, 97, 023510	2.5	48
139	Holographic writing of volume-type microgratings in silica glass by a single chirped laser pulse. *Applied Physics Letters*, **2002**, 81, 1137-1139	3.4	48
138	Thin Film Growth and Device Fabrication of Iron-Based Superconductors. *Journal of the Physical Society of Japan*, **2012**, 81, 011011	1.5	47
137	Simple Analytical Model of On Operation of Amorphous InGaZnO Thin-Film Transistors. *IEEE Transactions on Electron Devices*, **2011**, 58, 3463-3471	2.9	47
136	Thin film fabrication of nano-porous 12CaO·7Al2O3 crystal and its conversion into transparent conductive films by light illumination. *Thin Solid Films*, **2003**, 445, 309-312	2.2	47
135	Functions of heteromeric association between adenosine and P2Y receptors. *Journal of Molecular Neuroscience*, **2005**, 26, 233-8	3.3	47
134	Comprehensive studies on the stabilities of a-In-Ga-Zn-O based thin film transistor by constant current stress. *Thin Solid Films*, **2010**, 518, 3012-3016	2.2	45
133	Opto-electronic properties and light-emitting device application of widegap layered oxychalcogenides: LaCuOCh (Ch = chalcogen) and La2CdO2Se2. *Physica Status Solidi (A) Applications and Materials Science*, **2006**, 203, 2800-2811	1.6	45
132	Antiferromagnetic bipolar semiconductor LaMnPO with ZrCuSiAs-type structure. *Journal of Applied Physics*, **2009**, 105, 093916	2.5	44
131	Roles of Hydrogen in Amorphous Oxide Semiconductor In-Ga-Zn-O: Comparison of Conventional and Ultra-High-Vacuum Sputtering. *ECS Journal of Solid State Science and Technology*, **2014**, 3, Q3085-Q3090	2	43
130	Operation Characteristics of Thin-Film Transistors Using Very Thin Amorphous InGaZnO Channels. *Electrochemical and Solid-State Letters*, **2011**, 14, H197		43

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128	High critical-current density with less anisotropy in BaFe2(As,P)2 epitaxial thin films: Effect of intentionally grown c-axis vortex-pinning centers. *Applied Physics Letters*, **2014**, 104, 182603	3.4	41
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126	Identical effects of indirect and direct electron doping of superconducting BaFe2As2 thin films. *Physical Review B*, **2012**, 85,	3.3	41
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124	Device applications of transparent oxide semiconductors: Excitonic blue LED and transparent flexible TFT. *Journal of Electroceramics*, **2006**, 17, 267-275	1.5	41
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121	Photoluminescence from Au ion-implanted nanoporous single-crystal 12CaO7Al2O3. *Physical Review B*, **2006**, 73,	3.3	39
120	Field-Induced Current Modulation in Nanoporous Semiconductor, Electron-Doped 12CaO7Al2O3. *Chemistry of Materials*, **2005**, 17, 6311-6316	9.6	39
119	Heteroepitaxial film growth of layered compounds with the ZrCuSiAs-type and ThCr2Si2-type structures: From Cu-based semiconductors to Fe-based superconductors. *Physica C: Superconductivity and Its Applications*, **2009**, 469, 657-666	1.3	37
118	Origins of hole doping and relevant optoelectronic properties of wide gap p-type semiconductor, LaCuOSe. *Journal of the American Chemical Society*, **2010**, 132, 15060-7	16.4	36
117	Heteroepitaxial growth of layered semiconductors, LaZnOPn (Pn = P and As). *Thin Solid Films*, **2008**, 516, 5800-5804	2.2	36
116	Amorphous SnGaZnO channel thin-film transistors. *Physica Status Solidi (A) Applications and Materials Science*, **2008**, 205, 1920-1924	1.6	34
115	Band alignment of InGaZnO4/Si interface by hard x-ray photoelectron spectroscopy. *Journal of Applied Physics*, **2012**, 112, 033713	2.5	33
114	Sn[sub 0.9]In[sub 0.1]P[sub 2]O[sub 7]-Based Organic/Inorganic Composite Membranes. *Journal of the Electrochemical Society*, **2007**, 154, B63	3.9	33
113	Synthesis of single-phase layered oxychalcogenide La2CdO2Se2: crystal structure, optical and electrical properties. *Journal of Materials Chemistry*, **2004**, 14, 2946		33
112	Wide gap p-type degenerate semiconductor: Mg-doped LaCuOSe. *Thin Solid Films*, **2003**, 445, 304-308	2.2	33

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110	Superconductivity in noncentrosymmetric ternary equiatomic pnictides LaMP (M = Ir and Rh; P = P and As). *Physical Review B*, **2014**, 89,	3.3	32
109	Control of carrier concentration and surface flattening of CuGaO2 epitaxial films for a p-channel transparent transistor. *Thin Solid Films*, **2008**, 516, 5790-5794	2.2	32
108	Effects of low-temperature ozone annealing on operation characteristics of amorphous InGaZnO thin-film transistors. *Thin Solid Films*, **2012**, 520, 3787-3790	2.2	30
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106	Doping effects in amorphous oxides. *Journal of the Ceramic Society of Japan*, **2012**, 120, 447-457	1	30
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103	Optical Properties and Two-Dimensional Electronic Structure in Wide-Gap Layered Oxychalcogenide: La2CdO2Se2. *Journal of Physical Chemistry B*, **2004**, 108, 17344-17351	3.4	30
102	LaCo2B2: a Co-based layered superconductor with a ThCr2Si2-type structure. *Physical Review Letters*, **2011**, 106, 237001	7.4	29
101	Film Texture, Hole Transport and Field-Effect Mobility in Polycrystalline SnO Thin Films on Glass. *ECS Journal of Solid State Science and Technology*, **2014**, 3, Q3040-Q3044	2	28
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97	Solid State Syntheses of 12SrO 7Al2O3 and Formation of High Density Oxygen Radical Anions, O and O2 *Chemistry of Materials*, **2008**, 20, 5987-5996	9.6	27
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91	Optimization of Transparent Conductive Oxide for Improved Resistance to Reactive and/or High Temperature Optoelectronic Device Processing. *Japanese Journal of Applied Physics*, **1999**, 38, 5796-5804	1.4	25
90	Magnetic structure and electromagnetic properties of LnCrAsO with a ZrCuSiAs-type structure (Ln = La, Ce, Pr, and Nd). *Inorganic Chemistry*, **2013**, 52, 13363-8	5.1	23
89	Thin film and bulk fabrication of room-temperature-stable electride C12A7:e□utilizing reduced amorphous 12CaO□7Al2O3(C12A7). *Journal of Non-Crystalline Solids*, **2008**, 354, 2772-2776	3.9	23
88	Critical factor for epitaxial growth of cobalt-doped BaFe2As2 films by pulsed laser deposition. *Applied Physics Letters*, **2014**, 104, 172602	3.4	22
87	Anion Incorporation-induced Cage Deformation in 12CaO□7Al2O3Crystal. *Chemistry Letters*, **2007**, 36, 902-903	1.7	22
86	Electron injection barriers between air-stable electride with low work function, C12A7:e□and pentacene, C60 and copper phthalocyanine. *Journal of Materials Chemistry*, **2012**, 22, 4278		21
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84	Electronic insulator-conductor conversion in hydride ion-doped 12CaO□7Al2O3 by electron-beam irradiation. *Applied Physics Letters*, **2005**, 86, 022109	3.4	21
83	Creation of new functions in transparent oxides utilizing nanostructures embedded in crystal and artificially encoded by laser pulses. *Semiconductor Science and Technology*, **2005**, 20, S92-S102	1.8	21
82	Control of grain-boundary tunneling barriers in polycrystalline silicon. *Applied Physics Letters*, **2002**, 81, 2388-2390	3.4	21
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